



Insulated Gate Bi-Polar Transistor Type T2000BB45G

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V _{CES}	Collector – emitter voltage	4500	V
V _{DC link}	Permanent DC voltage for 100 FIT failure rate.	2800	V
V _{GES}	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I _C	DC collector current, IGBT	2000	A
I _{CRM}	Repetitive peak collector current, t _p =1ms, IGBT	4000	A
I _{F(DC)}	Continuous DC forward current, Diode	2000	A
I _{FRM}	Repetitive peak forward current, t _p =1ms, Diode	4000	A
I _{FSM}	Peak non-repetitive surge t _p =10ms, V _{RM} =60%V _{RRM} , Diode (Note 4)	52.3	kA
I _{FSM2}	Peak non-repetitive surge t _p =10ms, V _{RM} ≤10V, Diode (Note 4)	57.5	kA
P _{MAX}	Maximum power dissipation, IGBT (Note 2)	15.5	kW
(di/dt) _{cr}	Critical diode di/dt (note 3)	4000	A/μs
T _j	Operating temperature range.	-40 to +125	°C
T _{stg}	Storage temperature range.	-40 to +125	°C

Notes: -

- 1) Unless otherwise indicated T_j = 125°C.
- 2) T_{sink} = 25°C, double side cooled.
- 3) Maximum commutation loop inductance 180nH.
- 4) Half-sinewave, 125°C T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
$V_{CE(sat)}$	Collector – emitter saturation voltage	-	2.7	3.1	$I_C = 2000A$, $V_{GE} = 15V$, $T_j = 25^\circ C$	V
		-	3.5	3.9	$I_C = 2000A$, $V_{GE} = 15V$	V
V_{T0}	Threshold voltage	-	-	1.76	Current range: 667A – 2000A	V
r_T	Slope resistance	-	-	1.07		mΩ
$V_{GE(TH)}$	Gate threshold voltage	-	5.1	-	$V_{CE} = V_{GE}$, $I_C = 205mA$	V
I_{CES}	Collector – emitter cut-off current	-	65	90	$V_{CE} = V_{CES}$, $V_{GE} = 0V$	mA
I_{GES}	Gate leakage current	-	-	±23	$V_{GE} = \pm 20V$	μA
C_{ies}	Input capacitance	-	317	-	$V_{CE} = 25V$, $V_{GE} = 0V$, $f = 1MHz$	nF
$t_{d(on)}$	Turn-on delay time	-	1.7	-	$I_C = 2000A$, $V_{CE} = 2800V$, $di/dt = 3500A/\mu s$ $V_{GE} = \pm 15V$, $L_s = 180nH$ $R_{g(ON)} = 2.7\Omega$, $R_{g(OFF)} = 12\Omega$, $C_{GE} = 220nF$ Integral diode used as freewheel diode (Note 3 & 4)	μs
$t_r(V)$	Rise time	-	3.8	-		μs
$Q_{g(on)}$	Turn-on gate charge	-	14.5	-		μC
E_{on}	Turn-on energy	-	14	-		J
$t_{d(off)}$	Turn-off delay time	-	5.5	-		μs
$t_f(I)$	Fall time	-	2.8	-		μs
$Q_{g(off)}$	Turn-off gate charge	-	11	-		μC
E_{off}	Turn-off energy	-	12.5	-		J
I_{SC}	Short circuit current	-	7800	-	$V_{GE} = +15V$, $V_{CC} = 2800V$, $V_{CEmax} \leq V_{CES}$, $t_p \leq 10\mu s$	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V_F	Forward voltage	-	3.35	3.65	$I_F = 2000A$, $T_j = 25^\circ C$	V
		-	3.55	3.85	$I_F = 2000A$	V
V_{T0}	Threshold voltage	-	-	2.08	Current range 667A - 2000A	V
r_T	Slope resistance	-	-	0.88		mΩ
I_{rm}	Peak reverse recovery current	-	2050	-	$I_F = 2000A$, $V_r = 2800V$, $V_{GE} = -15V$, $di/dt = 3500A/\mu s$	A
Q_{rr}	Recovered charge	-	2450	-		μC
t_{rr}	Reverse recovery time, 50% chord	-	1.6	-		μs
E_r	Reverse recovery energy	-	3.6	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R_{thJK}	Thermal resistance junction to sink, IGBT	-	-	6.45	Double side cooled	K/kW
		-	-	10.5	Collector side cooled	K/kW
		-	-	16.8	Emitter side cooled	K/kW
R_{thJK}	Thermal resistance junction to sink, Diode	-	-	9.65	Double side cooled	K/kW
		-	-	14.9	Cathode side cooled	K/kW
		-	-	27.4	Anode side cooled	K/kW
F	Mounting force	60	-	85	Note 2	kN
W_t	Weight	-	2.4	-		kg

Notes:-

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) Figures 6 to 9 are obtained using integral diode as freewheeling diode

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

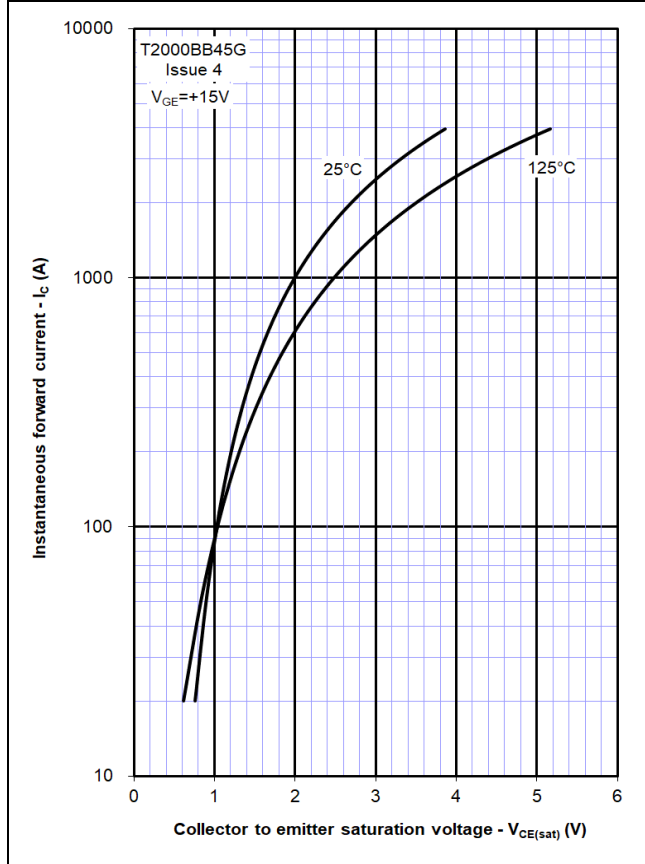


Figure 2 – Typical output characteristic

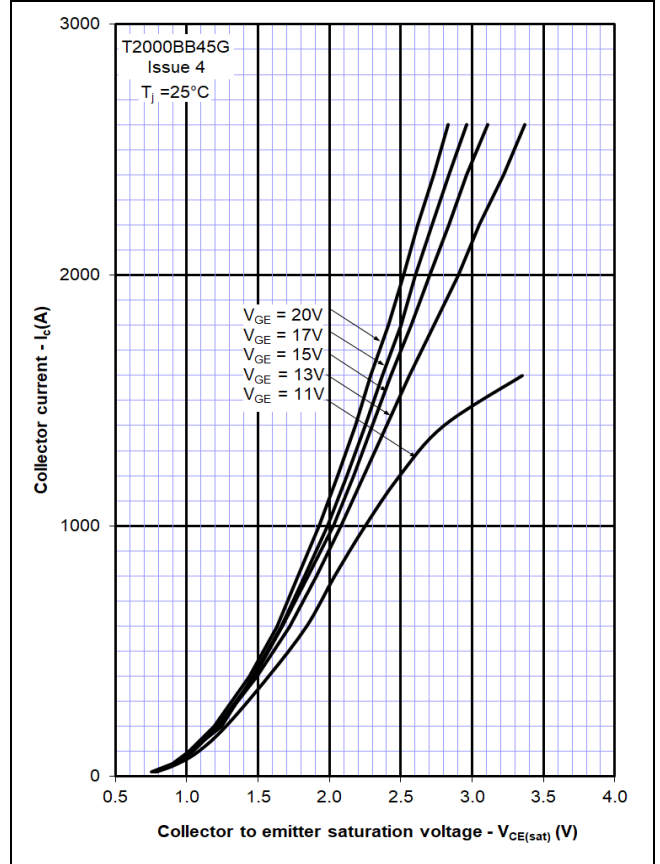


Figure 3 – Typical output characteristic

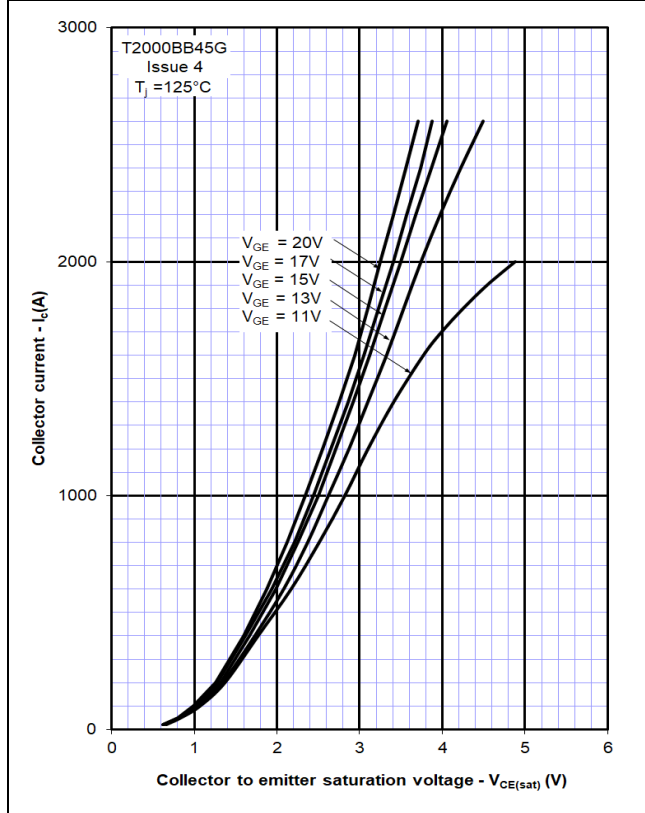


Figure 4 – Typical turn-on delay time vs gate resistance

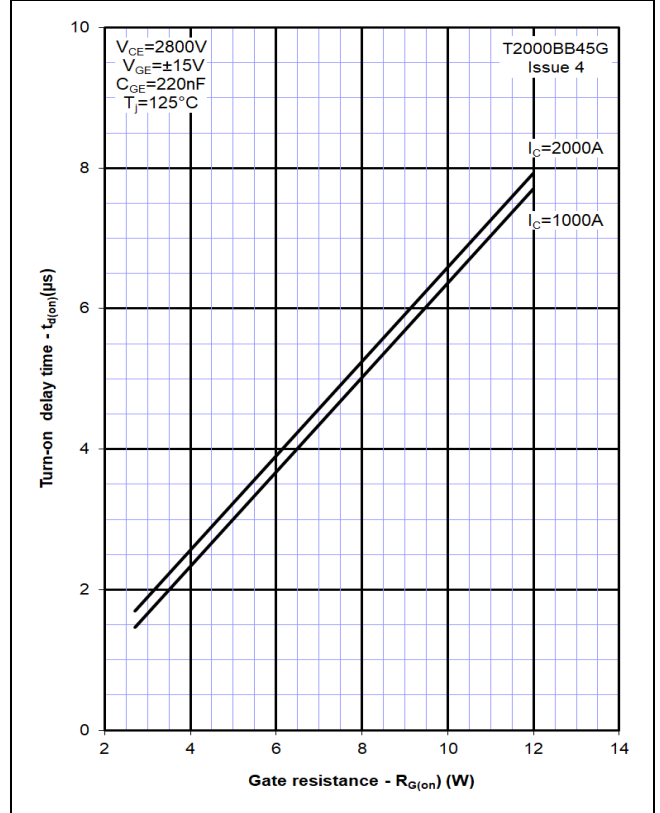


Figure 5 – Typical turn-off delay time vs. gate resistance

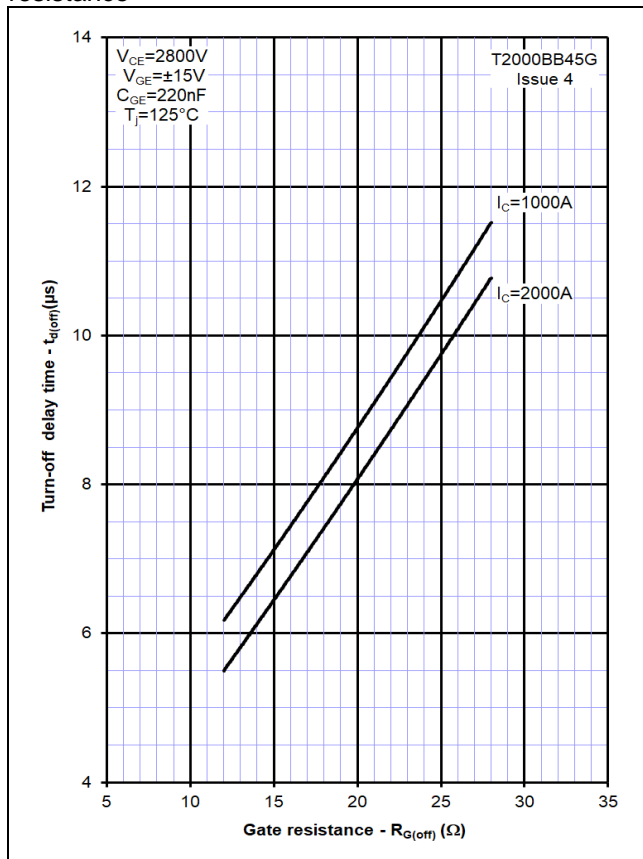


Figure 6 – Typical turn-on energy vs. collector current

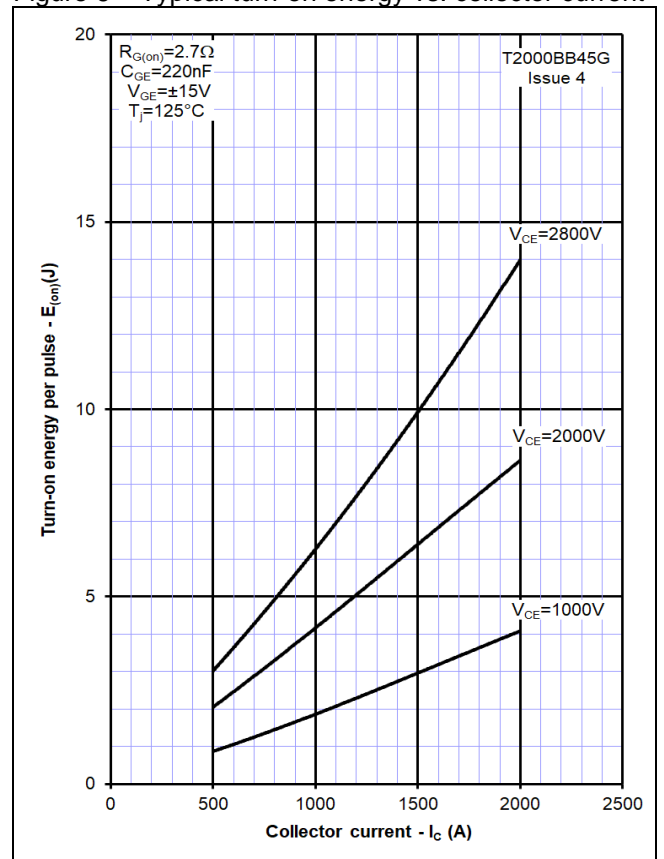


Figure 7 – Typical turn-on energy vs. di/dt

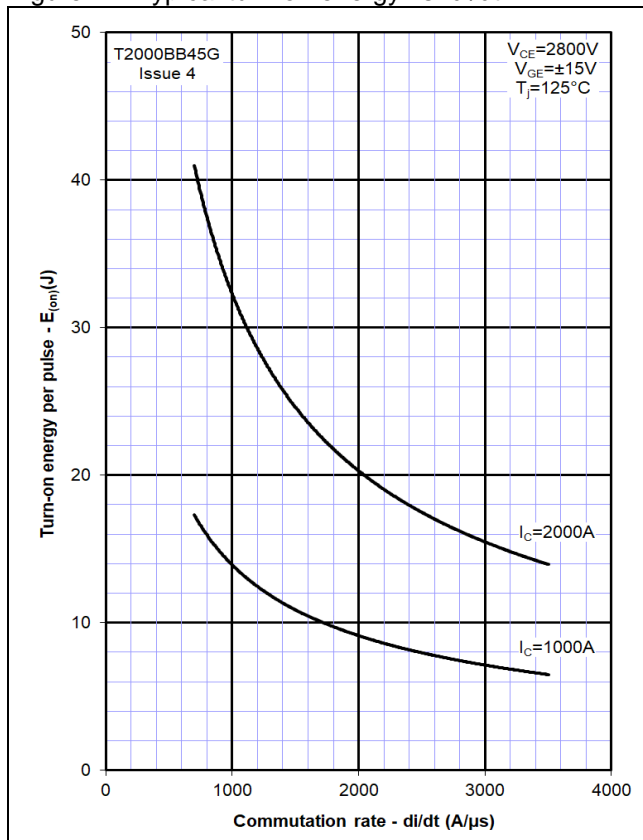


Figure 8 – Typical turn-off energy vs. collector current

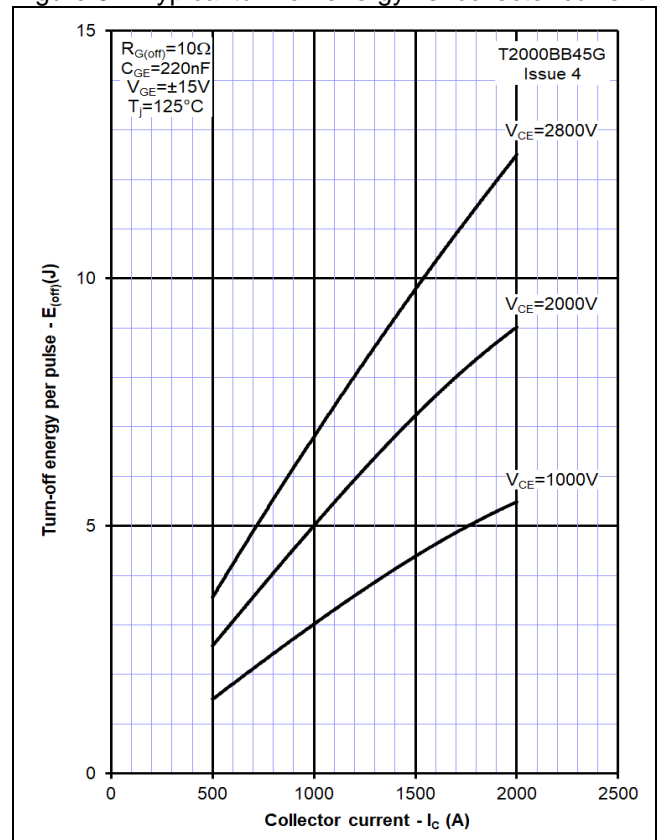


Figure 9 – Turn-off energy vs voltage

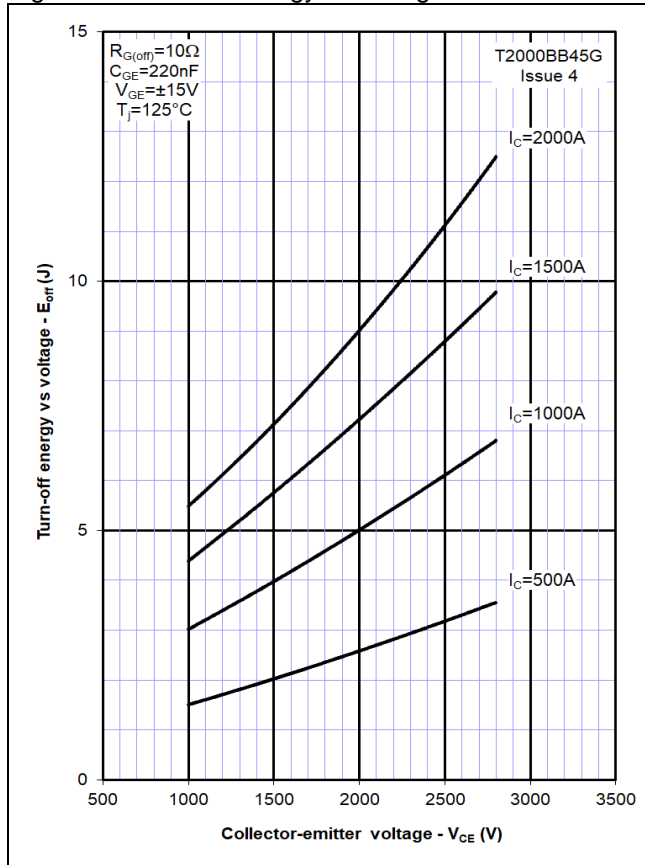


Figure 10 – Safe operating area (IGBT)

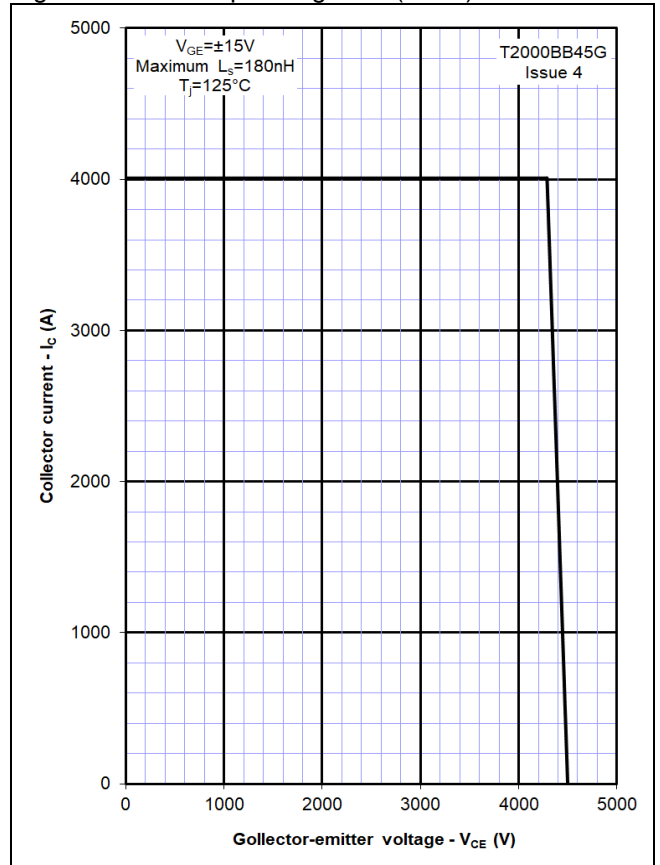


Figure 11 – Typical diode forward characteristics

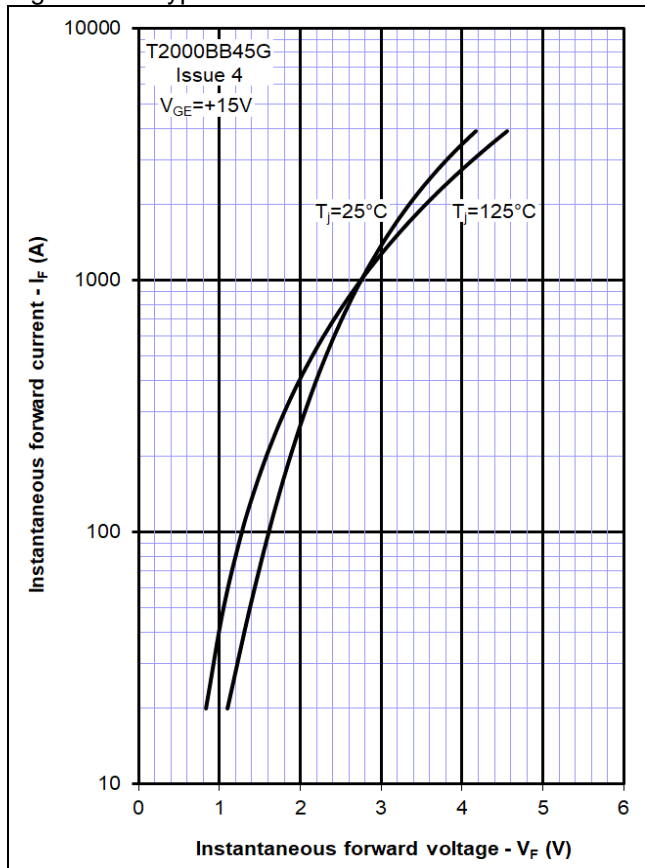


Figure 12 – Typical recovered charge

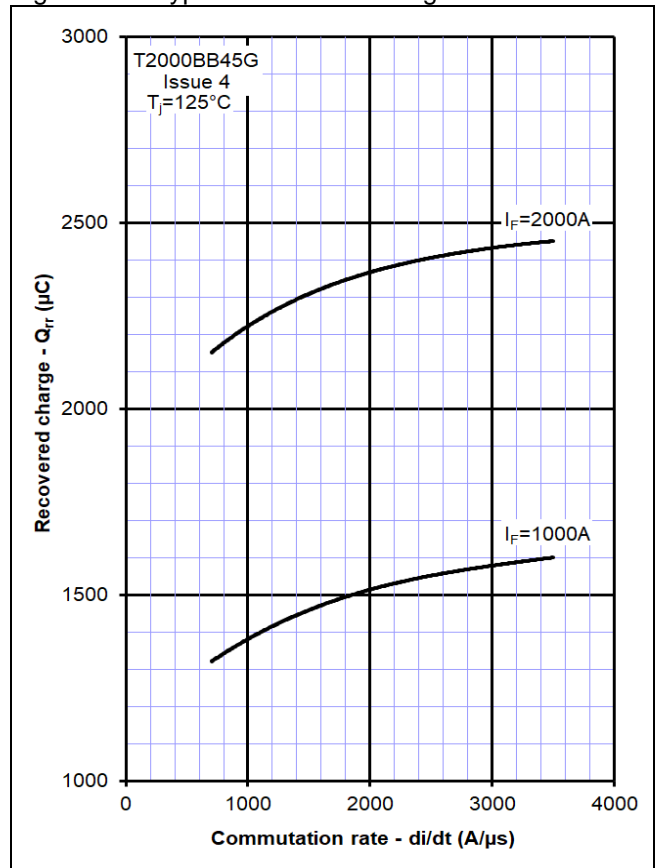


Figure 13 – Typical reverse recovery current

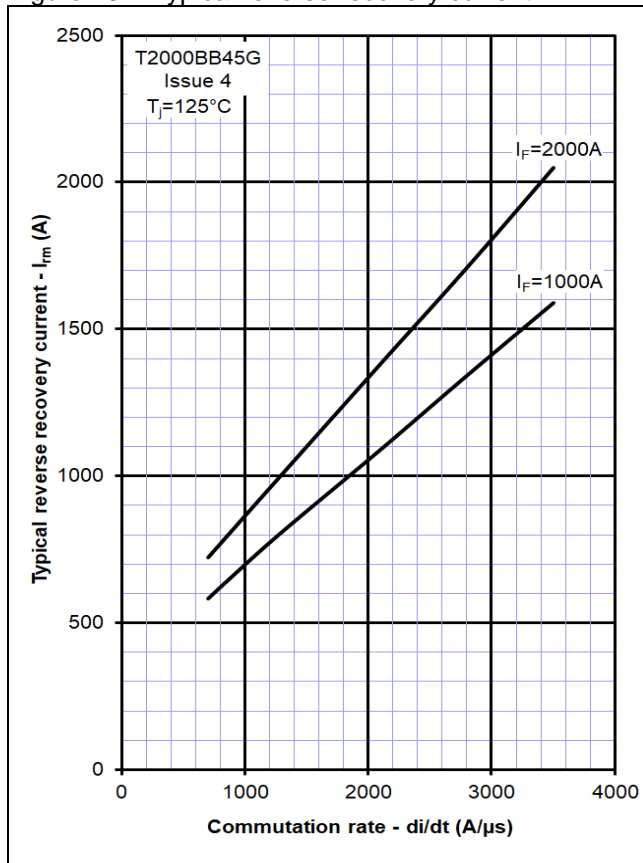


Figure 14 – Typical reverse recovery time

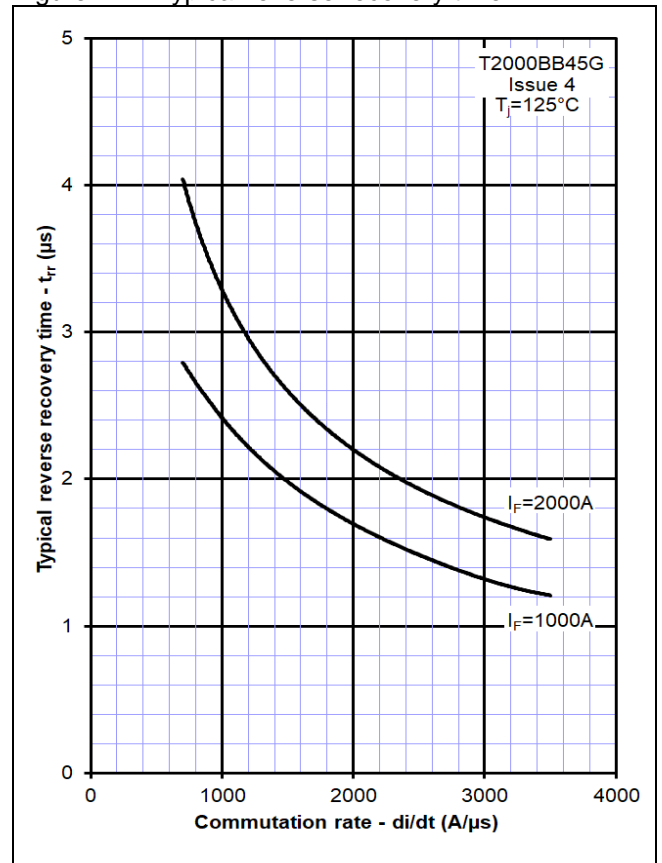


Figure 15 – Typical reverse recovery energy

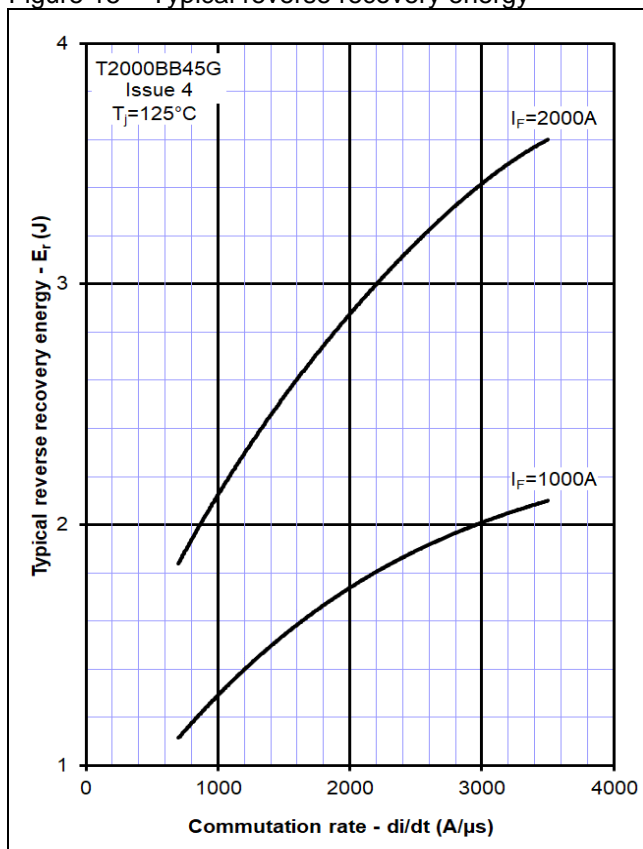


Figure 16 – Safe operating area (Diode)

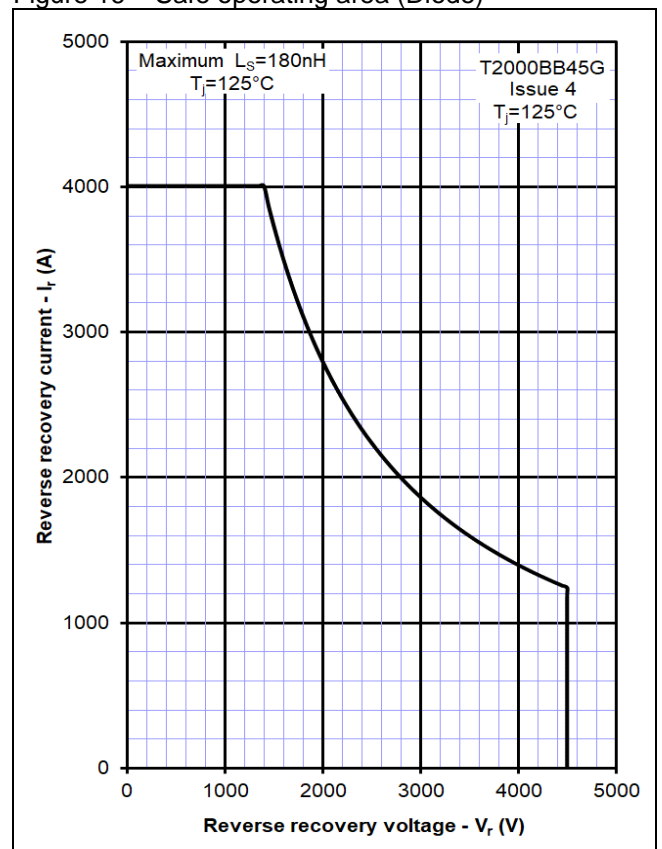


Figure 17 – Transient thermal impedance (IGBT)

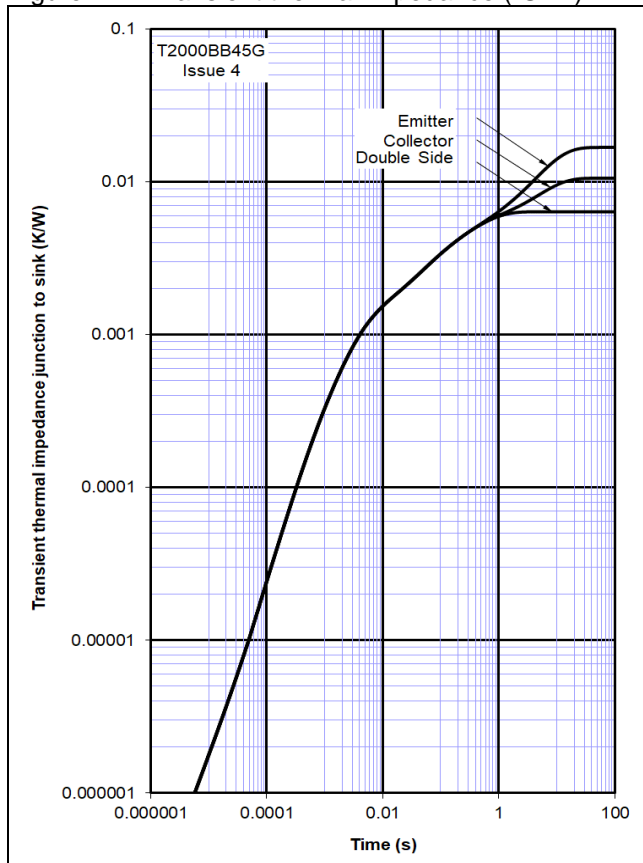
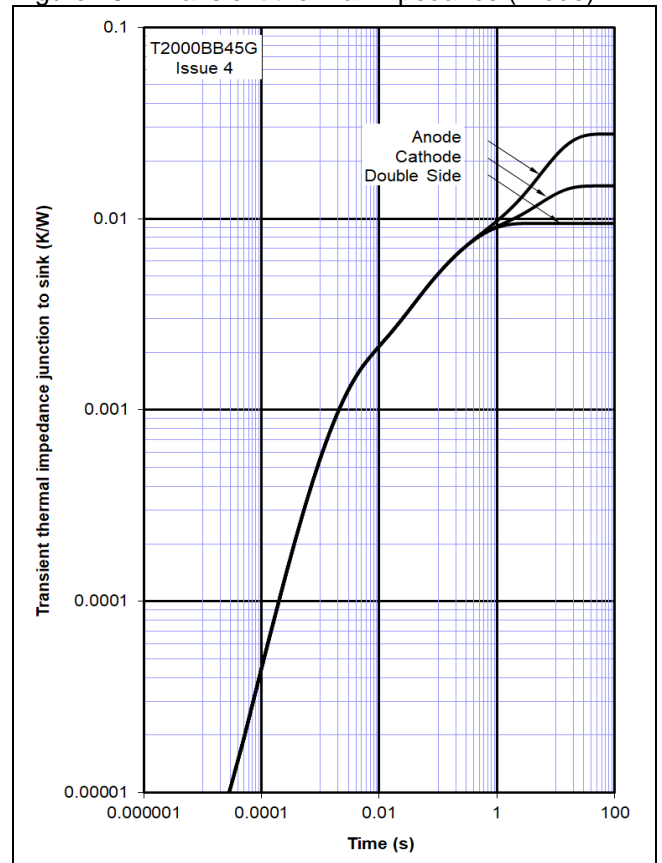
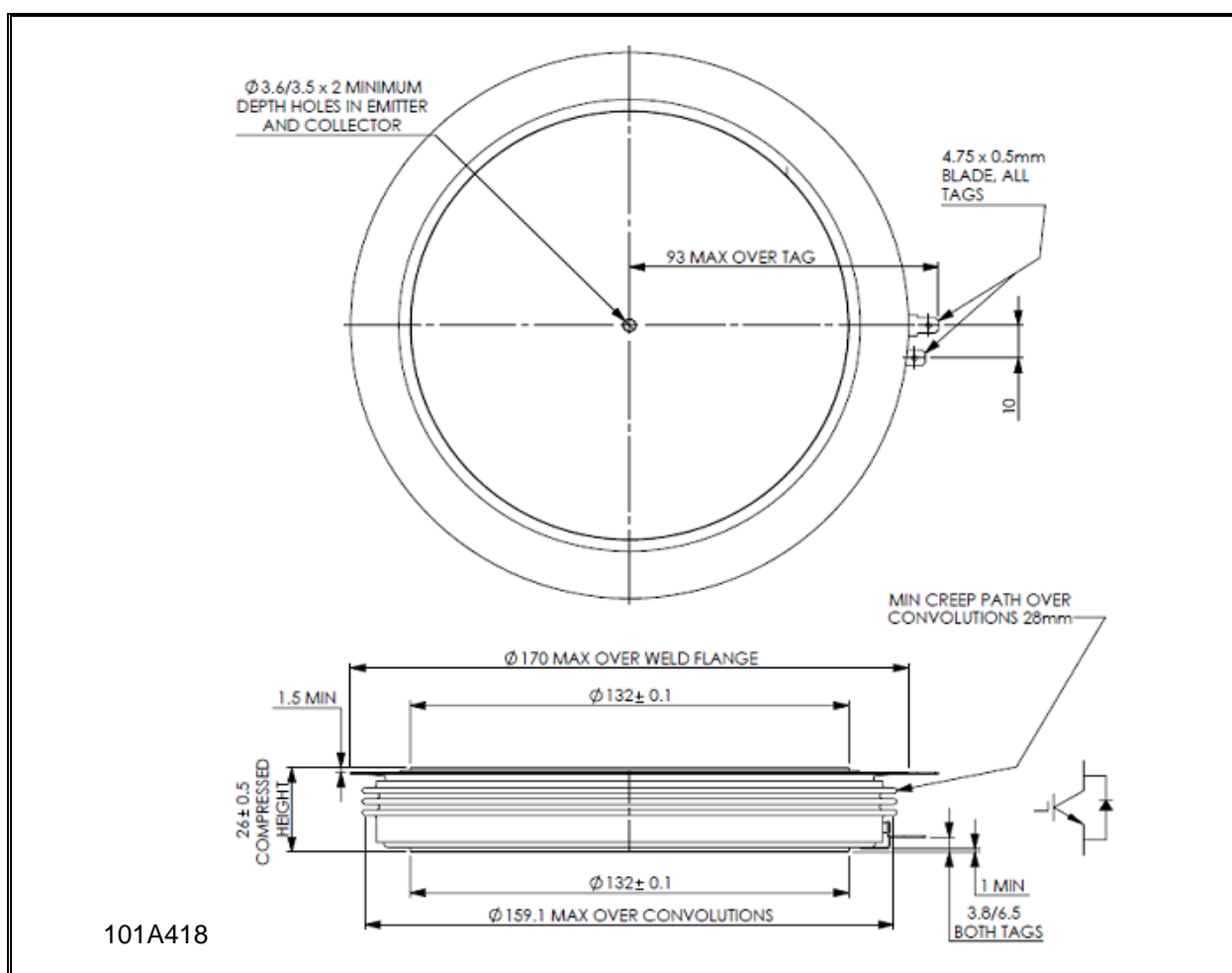


Figure 18 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

T2000	BB	45	G
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 45	Fixed format code

Typical order code: T2000BB45G ($V_{CES} = 4500V$)

IXYS Semiconductor GmbH

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de



IXYS
A Littelfuse Technology

IXYS UK Westcode Ltd

Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
E-mail: sales@ixysuk.com

IXYS Corporation

1590 Buckeye Drive
Milpitas CA 95035-7418
Tel: +1 (408) 457 9000
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

www.littelfuse.com

www.ixysuk.com

www.ixys.net

IXYS Long Beach

IXYS Long Beach, Inc
2500 Mira Mar Ave, Long Beach
CA 90815
Tel: +1 (562) 296 6584
Fax: +1 (562) 296 6585
Email: service@ixyslongbeach.com

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